

**PATENT APPLICATION**

Sheet 1 of 2

<p><b>FORM PTO-1449</b></p> <p><b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b></p> <p align="center">(Use several sheets if necessary)</p>	<p>ATTY. DOCKET NO. <b>200210020-1</b></p>	<p>APPLICATION NO.</p>	<p>CONFIRMATION NO.</p>
<p>APPLICANT <b>Novet et al.</b></p>			
<p>FILING DATE</p>		<p>GROUP</p>	

**REFERENCE DESIGNATION                      U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
<i>me</i>	1A	5,894,189	4/13/1999	Ogasawara et al.	
<i>me</i>	1B	6,285,118	9/4/2001	Hatal et al.	
	1C				
	1D				
	1E				
	1F				
	1G				
	1H				
	1I				
	1J				
	1K				

**FOREIGN PATENT DOCUMENTS**

	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	1L				
	1M				
	1N				
	1O				
	1P				

**OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)**

<i>me</i>	1Q	Sheng et al., "Efficient and Ballistic Cold Electron Emission from Porous Polycrystalline Silicon Diodes with a Porosity Multilayer Structure", J. Vac. Sci. Technol. B 19(1), Jan/Feb 2001, pp. 64-67.
<i>me</i>	1R	Kusunoki et al., "Increasing Emission Current from MIM Cathodes by Using an Ir-Pt-Au Multilayer Top Electrode", IEEE Transactions on Electron Devices, Vol. 47, No. 8, Aug 2000, pp. 1667-1672.
<i>me</i>	1S	Negishi et al., "High Efficiency Electron-Emission in Pt/SiOx/Si/Al Structure", Jpn. J. Appl. Phys., Vol. 36 (1997), pp L939-L941.

EXAMINER

*[Signature]*

DATE CONSIDERED

*1/9/05*

## PATENT APPLICATION

Sheet 2 of 2

<b>FORM PTO-1449</b>  <b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)	ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
	200210020-1		
	APPLICANT		
	Nov t t al.		
	FILING DATE	GROUP	

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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
	2A				
	2B				
	2C				
	2D				
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	2J				
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	2L					
	2M					
	2N					
	2O					
	2P					

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

102	2Q	Miyamoto et al., "MIS Emitter with Epitaxial CaF <sub>2</sub> Layer as Insulator", Technical Digest of IVMC'97 Kyongju, Korea, 1997, pp. 226-230.
	2R	
	2S	

EXAMINER

DATE CONSIDERED